

Reliability Physics of Wide Band Gap Semiconductor Devices



S&T Campaign: Materials Research Electronics (High Power)

Ken Jones: (301) 394-2005, Kenneth.A.Jones162.civ@mail.mil
Aivars Lelis: (301) 394-5426, Aivars.J.Lelis.civ@mail.mil
Nick Jankowski: (301) 394-2337, Nicholas.R.Jankowski.civ@mail.mil
Sasha Batyrev: (410) 306-4582, Iskander.G.Batyrev.civ@mail.mil

Research Objectives

- Determine how material and fabrication defects, as well as the temperature, affect the operation and reliability of WBG semiconductor devices

GaN CAVET

- Form Ohmic contact to high Al% AlGaIn layer
- Deposit thin AlN layer to reduce alloy scattering
- Create a p-type current blocking layer (CBL)
- Grow a low doped, high Al% AlGaIn drift region
- Use graded AlGaIn to reduce TDs created by mismatch
- Use high structural quality single crystal substrates

Burgers Vector

Glide Planes

AlGaIn Film

GaN Substrate

Defect Identification using Multi-scale Modeling:

SiC MOSFETS

Defect ID using Materials Analysis:

TEM, EELS:

ESR:

Multi-scale modeling:

DFT coupled w/ device simulator results—C interstitial is dominant Interface trap

Temperature Measurement

Device Thermal Profile and Gradients

Modeled hot spot in GaN-AlGaIn HEMT

ARL Expertise and Facilities for Supporting Collaborative Research

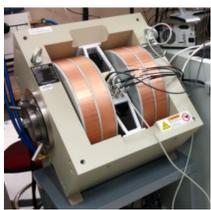
Materials Characterization



Double Crystal X-Ray System



DLTS System



Hall System

Device and Device Reliability Measurements

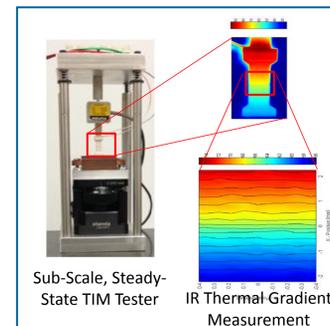


Semiconductor Parameter Analyzer with Automated BTI Testing

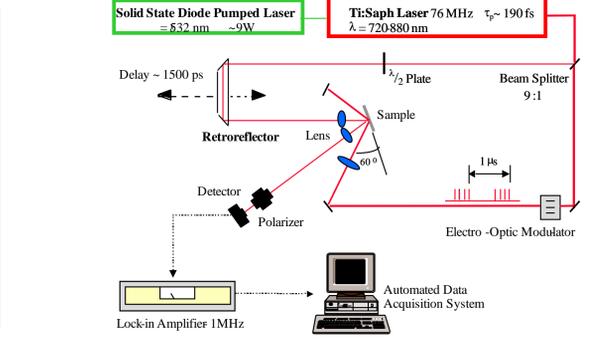


Dynamic High Temp Reverse Bias System (DHTRB)

Thermal Measurements



1D steady state TIM tester



Time Domain Thermoreflectance system

Expertise and Facilities Being Sought for Collaboration

- Knowledge of the physics of the operation of WBG devices and how their operation and reliability are affected by defects, and unique device measurement capabilities
- Knowledge of the physics of how defects are formed and ways to reduce their concentration and/or mitigate their negative effects, and unique equipment to measure their concentrations and properties
- Knowledge of the physics of thermal conduction and how it is affected by material defects and interfaces, and unique equipment to measure it
- Unique devices you want to be processed, and devices for which you want to be thoroughly characterized and their reliability measured
- Modelers of WBG devices, material defects and how the defects affect the properties of the components of the devices, and the thermal conduction and how the phonons are affected by defects and interfaces

Challenges

- Better understanding of the cause and effect of various crystalline and point defects in WBG materials and their associated insulating layers and interfaces on device performance and reliability
- More precisely identifying the interrelationships between electrical, mechanical and thermal domains within the device and how the interactions initiate failure modes.
- Developing physics based relationships between failure modes and initial device measurements, as well as how they are accelerated by increasing the temperature
- Delimiting between macroscopic diffusion and quantum mechanical ballistic transport as represented by phonons in heat conduction processes as devices become smaller